

## Rad Hard NPN Silicon High Speed Switching Transistor

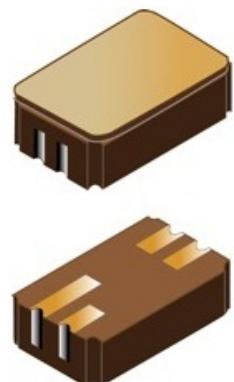
**Screened per MIL-PRF-19500 & ESCC 22900**

Screened Levels:  
MSR

QPL RANGE and RAD LEVEL	
Radiation Level	MSR2N2369AUA
TID	100 Krad
ELDRS	100 Krad
DESCRIPTION	

This RHA level high speed NPN switching transistor, 2N2369A in a UA package, is ideal to drive many high-reliability applications. This device is constructed and screened to a JANSR performance level with radiation test method 1019 wafer lot acceptance conducted on all die lots. Fully compliant to **GSFC EEE-INST-002** reliability, screening and radiation hardness assurance requirements for space flight projects

**Important:** For the latest information, visit our website <http://www.microsemi.com>.



### FEATURES

- JEDEC registered 2N2369A
- TID level screened per MIL-PRF-19500
- Also available with ELDRS testing to 0.01 Rad(s)/ sec
- MKCR / MHCR chip die available
- RHA (Radiation hardness assured) lot by lot validation testing via ELDR 0.1 Rad (SI)/sec dose rate

APPLICATIONS / BENEFITS
<ul style="list-style-type: none"> <li>Rad-Hard power supplies</li> <li>Rad-Hard motor controls</li> <li>General purpose switching</li> <li>Instrumentation Amps</li> <li>EPS Satellite switching power applications</li> </ul>

### UA Package

#### Also available in:



### MAXIMUM RATINGS @ $T_A = +25^\circ\text{C}$ unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	$T_J$ and $T_{STG}$	-65 to +200	$^\circ\text{C}$
Thermal Resistance Junction-to-Solder Pad	$R_{eJSP}$	210	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-to-Ambient	$R_{eJA}$	486	$^\circ\text{C}/\text{W}$
Total Power Dissipation:	$P_T$	0.36	W
@ $T_A = +25^\circ\text{C}$ <sup>(1)</sup>		0.36	
@ $T_C = +125^\circ\text{C}$ <sup>(2)(3)</sup>		0.36	
@ $T_{SP} = +125^\circ\text{C}$ <sup>(2)</sup>		0.36	
Collector-Base Voltage, Emitter Open	$V_{CBO}$	40	V
Emitter-Base Voltage, Collector Open	$V_{EBO}$	4.5	V
Collector-Emitter Voltage, Base Open	$V_{CEO}$	15	V
Collector Current, dc	$V_{CES}$	40	V
Solder Temperature @ 10 s	$T_{SP}$	260	$^\circ\text{C}$

**Notes:**

- Derate linearly 2.06 mW/ $^\circ\text{C}$  above  $T_A = +25^\circ\text{C}$ .
- Derate linearly 4.8 mW/ $^\circ\text{C}$  above  $T_C = +125^\circ\text{C}$ . See [Figures 1 and 2](#).
- Power dissipation limited to 360 mW per chip regardless of thermal resistance.

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#### MSC – Ireland

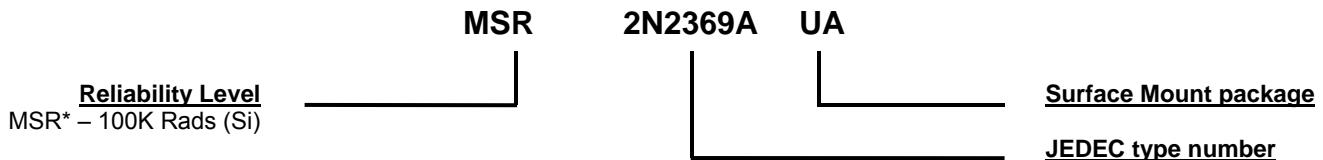
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[www.microsemi.com](http://www.microsemi.com)

**MECHANICAL and PACKAGING**

- CASE: Hermetically sealed ceramic package
- TERMINALS: Gold plate over nickel
- MARKING: Manufacturer's ID, date code, part number
- POLARITY: NPN (see package outline)
- TAPE & REEL option: Per EIA-481 (consult factory for quantities)
- WEIGHT: Approximately 0.12 grams
- See [Package Dimensions](#) on last page.

**PART NOMENCLATURE**


\*The MSR designator is our internal part nomenclature assigned to this family of parts, in lieu of pending JANSR submissions through DLA (Defense Logistic Agency).

**SYMBOLS & DEFINITIONS**

Symbol	Definition
$I_B$	Base current: The value of the dc current into the base terminal.
$I_C$	Collector current: The value of the dc current into the collector terminal.
$I_E$	Emitter current: The value of the dc current into the emitter terminal.
$R_G$	Gate drive impedance or Gate resistance
$V_{CB}$	Collector-base voltage: The dc voltage between the collector and the base.
$V_{CBO}$	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
$V_{CE}$	Collector-emitter voltage: The dc voltage between the collector and the emitter.
$V_{CEO}$	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
$V_{EB}$	Emitter-base voltage: The dc voltage between the emitter and the base
$V_{EBO}$	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

**ELECTRICAL CHARACTERISTICS @  $T_A = 25^\circ\text{C}$  unless otherwise noted.**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mA}$	$V_{(\text{BR})\text{CEO}}$	15		V
Collector-Base Cutoff Current $V_{CB} = 40 \text{ V}$ $V_{CB} = 32 \text{ V}$	$I_{CBO}$		10 0.2	$\mu\text{A}$
Emitter-Base Cutoff Current $V_{EB} = 4.5 \text{ V}$ $V_{EB} = 4.0 \text{ V}$	$I_{EBO}$		10 0.25	$\mu\text{A}$
Collector-Emitter Cutoff Current $V_{CE} = 20 \text{ V}$	$I_{CES}$		0.4	$\mu\text{A}$
<b>ON CHARACTERISTICS<sup>(1)</sup></b>				
Forward-Current Transfer Ratio $I_C = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $I_C = 30 \text{ mA}, V_{CE} = 0.4 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	$h_{FE}$	40 30 40 20	120 120 120 120	
Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$	$V_{CE(\text{sat})}$		0.2 0.25	V
Base-Emitter Voltage $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$	$V_{BE(\text{sat})}$	0.7	0.85 0.90	V

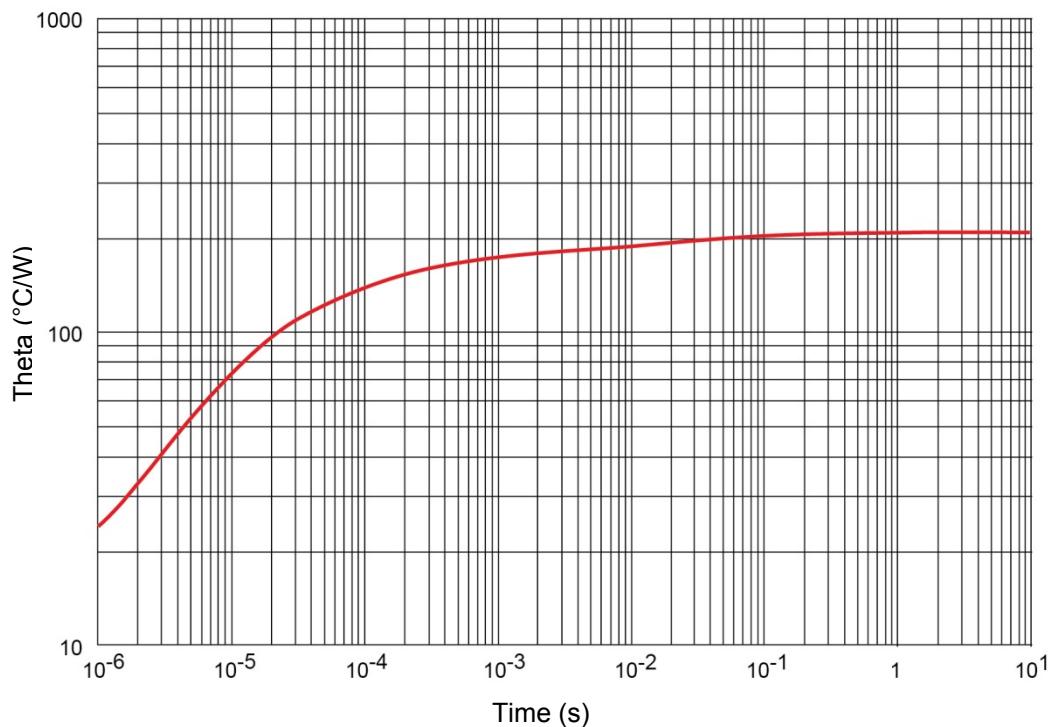
**DYNAMIC CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}, f = 1.0 \text{ kHz}$	$h_{fe}$	20		
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}, f = 100 \text{ MHz}$	$ h_{fe} $	5.0	10	
Output Capacitance $V_{CB} = 5 \text{ V}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	$C_{obo}$		4.0	pF
Input Capacitance $V_{EB} = 0.5 \text{ V}, I_C = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	$C_{ibo}$		5.0	pF

(1) Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**ELECTRICAL CHARACTERISTICS @  $T_A = +25^\circ\text{C}$ , unless otherwise noted (continued)**
**SWITCHING CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time $I_C = 10 \text{ mA}, I_{B1} = 3.0 \text{ mA}, I_{B2} = -1.5 \text{ mA}$	$t_{on}$		12	ns
Turn-Off Time $I_C = 10 \text{ mA}, I_{B1} = 3.0 \text{ mA}, I_{B2} = -1.5 \text{ mA}$	$t_{off}$		18	ns

**GRAPHS**

**FIGURE 1**  
Thermal Impedance Graph ( $R_{\Theta, \text{JSP}}$ )

### Radiation hardness assurance

The MSR series product are guaranteed in radiation with full compliance to MIL-PRF-19500 specification JANSR level and are also guaranteed to meet ESCC 22900 specifications (General specifications).

### Radiation assurance MIL-PRF-19500

MSR parts are guaranteed at 100 krad (Si), tested, in full compliancy with the MIL-PRF-19500 specification, specifically the Group D, subgroup 2 inspection, between 50 and 300 rad/s. All test are performed in accordance to MIL-PRF-19500 and test method 1019 of MIL-STD-750 for total Ionizing dose.

- Each wafer of each lot is tested, (note 1). The table below provides for each monitored parameters of the test conditions and the acceptance criteria

### **Radiation summary**

Radiation test (Note 1)	100 krad ESCC
Wafer test	each
Part tested	10 biased + 10 unbiased
Dose rate	0.1 rad/s
Acceptance	MIL-STD-750 method 1019
Displacement damage	Optional

1. Microsemi MSR products will exceed required testing of *ESCC basic specification 22900*

### **ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$ , unless otherwise noted (continued)**

#### **POST RADIATION**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Collector to Base Cutoff Current $V_{CB} = 40\text{ V}$ $V_{CB} = 32\text{ V}$	$I_{CBO}$		20 0.4	$\mu\text{A}$
Emitter to Base Cutoff Current $V_{EB} = 4.5\text{ V}$ $V_{EB} = 4\text{ V}$	$I_{EBO}$		20 0.50	$\mu\text{A}$
Collector to Emitter Breakdown Voltage $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	15		V
Forward-Current Transfer Ratio <sup>(2)</sup> $I_C = 10\text{ mA}, V_{CE} = 0.35\text{ V}$ $I_C = 30\text{ mA}, V_{CE} = 0.4\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$	$[h_{FE}]$	[20] [15] [20] [10]	120 120 120 120	
Collector-Emitter Saturation Voltage $I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 30\text{ mA}, I_B = 3.0\text{ mA}$	$V_{CE(sat)}$		0.23 0.29	V
Base-Emitter Saturation Voltage $I_C = 10\text{ mA}, I_B = 1.0\text{ mA}$ $I_C = 30\text{ mA}, I_B = 3.0\text{ mA}$	$V_{BE(sat)}$	0.70	0.98 1.04	V

(2) See method 1019 of MIL-STD-750 for how to determine  $[h_{FE}]$  by first calculating the delta ( $1/h_{FE}$ ) from the pre- and post-radiation  $h_{FE}$ . Notice the  $[h_{FE}]$  is not the same as  $h_{FE}$  and cannot be measured directly. The  $[h_{FE}]$  value can never exceed the pre-radiation minimum  $h_{FE}$  that it is based upon.

### ESCC radiation assurance

Each product lot is tested according to the ESCC basic specification 22900, with a minimum of 21 samples per diffusion lot and 10 samples per wafer, one sample being kept as un-irradiated sample, all of them being fully compliant with the applicable ESCC generic and/or detailed specification.

- Test of 10 pieces by wafer, 10 biased at least 80% of V(BR)CEO, 10 unbiased and 1 kept for reference
- Irradiation at 0.1 rad (Si)/s
- Acceptance criteria of each individual wafer if at least 100 krad guaranteed if all 20 samples comply with the post radiation electrical characteristics provided in [Table 4](#) (post radiation electrical characteristics for the 2N2369AUA)

Delivery together with the parts of the radiation verification test (RVT) report of the particular wafer used to manufacture the products. This RVT includes the value of each parameter at 30, 50, 70 and 100 krad (Si) and after 24 hour annealing at room temperature and after an additional 168 hour annealing at 100°C.

### Radiation summary

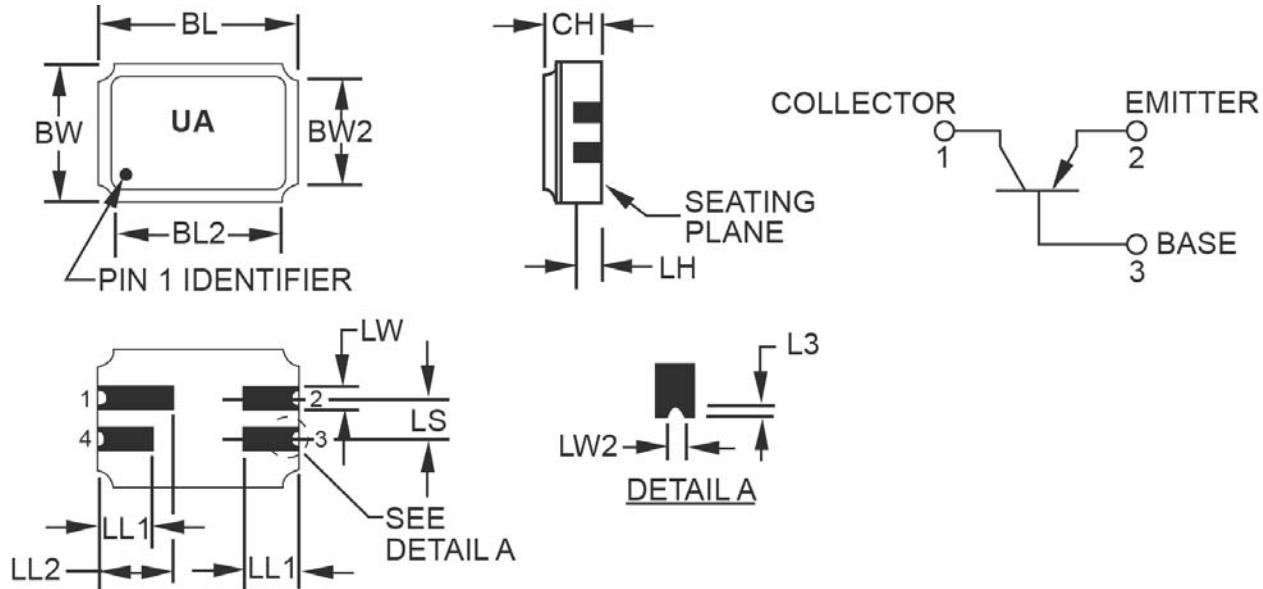
Radiation test (Note 1)	100 krad ESCC
Wafer test	each
Part	10 biased + 10 unbiased
Dose rate	0.1 rad/s
Acceptance	MIL-STD-750 method 1019
Displacement damage	Optional

1. Microsemi MSR products will exceed required testing of *ESCC basic specification 22900*

**POST RADIATION- Table 4**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Collector to Base Cutoff Current $V_{CB} = 40$ V $V_{CB} = 32$ V	$I_{CBO}$		20 0.4	$\mu$ A
Emitter to Base Cutoff Current $V_{EB} = 4.5$ V $V_{EB} = 4$ V	$I_{EBO}$		20 0.50	$\mu$ A
Collector to Emitter Breakdown Voltage $I_C = 10$ mA	$V_{(BR)CEO}$	15		V
Forward-Current Transfer Ratio <sup>(2)</sup> $I_C = 10$ mA, $V_{CE} = 0.35$ V $I_C = 30$ mA, $V_{CE} = 0.4$ V $I_C = 10$ mA, $V_{CE} = 1.0$ V $I_C = 100$ mA, $V_{CE} = 1.0$ V	$[h_{FE}]$	[20] [15] [20] [10]	120 120 120 120	
Collector-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 30$ mA, $I_B = 3.0$ mA	$V_{CE(sat)}$		0.23 0.29	V
Base-Emitter Saturation Voltage $I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 30$ mA, $I_B = 3.0$ mA	$V_{BE(sat)}$	0.70	0.98 1.04	V

1. This value is determined from  $\Delta(1/hfe)$  using pre & post radiation values of hfe.  $[hfe]$  should not exceed the pre- radiation minimum hfe..

**PACKAGE DIMENSIONS**

**NOTES:**

1. Dimensions are in inches.
2. Millimeters are given for information only.
3. Dimension "CH" controls the overall package thickness. When a window lid is used, dimension "CH" must increase by a minimum of 0.010 inch (0.254 mm) and a maximum of 0.040 inch (1.020 mm).
4. The corner shape (square, notch, radius, etc.) may vary at the manufacturer's option, from that shown on the drawing.
5. Dimensions "LW2" minimum and "L3" minimum and the appropriate castellation length define an unobstructed three-dimensional space traversing all of the ceramic layers in which a castellation was designed. (Castellations are required on bottom two layers, optional on top ceramic layer.) Dimension "LW2" maximum and "L3" maximum define the maximum width and depth of the castellation at any point on its surface. Measurement of these dimensions may be made prior to solder dipping.
6. The co-planarity deviation of all terminal contact points, as defined by the device seating plane, shall not exceed 0.006 inch (0.15mm) for solder dipped leadless chip carriers.
7. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi x$  symbology.

Symbol	Dimensions				Note	
	Inch		Millimeters			
	Min	Max	Min	Max		
BL	0.215	0.225	5.46	5.71		
BL2	-	0.225	-	5.71		
BW	0.145	0.155	3.68	3.93		
BW2	-	0.155	-	3.93		
CH	0.061	0.075	1.55	1.90	3	
L3	0.003	0.007	0.08	0.18	5	
LH	0.029	0.042	0.74	1.07		
LL1	0.032	0.048	0.81	1.22		
LL2	0.072	0.088	1.83	2.23		
LS	0.045	0.055	1.14	1.39		
LW	0.022	0.028	0.56	0.71		
LW2	0.006	0.022	0.15	0.56	5	
Pin no.						
Transistor						
		1	2	3	4	
		Collector	Emitter	Base	N/C	

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